



## 1.0A MOSFET/IGBT Gate Driver Optocoupler

### Features

- Peak Output Current : IOP = ±1.0A (max)
- Threshold Input Current: IFLH = 5 mA (max)
- Common mode transient immunity : ±20kV/μs (min)
- Under voltage lock out (UVLO) protection with hysteresis
- Regulatory Approvals
  - UL - UL1577 (E364000)
  - VDE - EN60747-5-5(VDE0884-5) (Pending Approval)
  - CQC – GB4943.1, GB8898
  - IEC60065, IEC60950

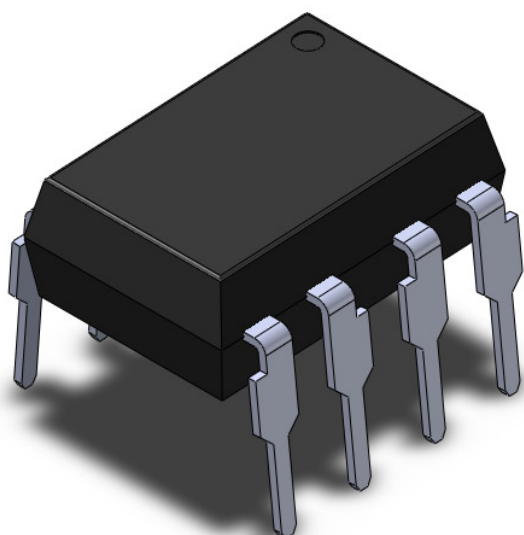
### Description

The CT3150 consists of a GaAsP LED optically coupled to an integrated circuit with a power output stage. This optocoupler is ideally suited for driving power IGBTs and MOSFETs used in motor control inverter applications. The high operating voltage range of the output stage provides the drive voltages required by gate controlled devices.

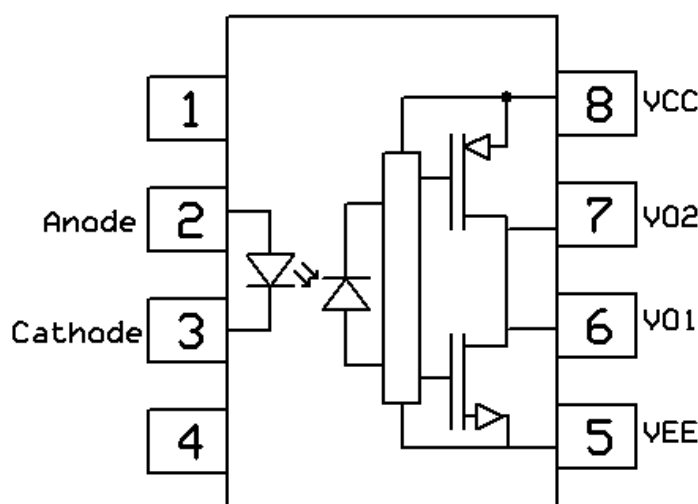
### Applications

- Isolated IGBT/Power MOSFET gate drive
- Industrial Inverter
- AC brushless and DC motor drives
- Induction Heating

### Package Outline



### Schematic



Note: Different lead forming options available. See package dimension.



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## Truth Table

LED	V <sub>CC</sub> -V <sub>EE</sub> Positive Going	V <sub>CC</sub> -V <sub>EE</sub> Negative Going	Output
Off	0 to 30 V	0 to 30V	Low
On	0 to 6.5V	0 to 6V	Low
On	6.5 to 8.3V	6 to 8V	Transition
On	8.3 to 30V	8 to 30V	High

## Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
V <sub>ISO</sub>	Isolation voltage	5000	V <sub>RMS</sub>	1
T <sub>OPR</sub>	Operating temperature	-40 ~ +100	°C	
T <sub>STG</sub>	Storage temperature	-55 ~ +125	°C	
T <sub>SOL</sub>	Soldering temperature	260	°C	2
P <sub>T</sub>	Total Power Dissipation	300	mW	
f <sub>OPR</sub>	Operating Frequency	50	kHz	3
<b>Emitter</b>				
I <sub>F</sub>	Forward current	25	mA	
I <sub>FP</sub>	Peak forward current (50% duty, 1ms P.W)	1	A	
V <sub>R</sub>	Reverse voltage	5	V	
P <sub>I</sub>	Input Power dissipation	45	mW	
<b>Detector</b>				
P <sub>O</sub>	Output Power dissipation	250	mW	
V <sub>O(PEAK)</sub>	Peak Output Voltage	35	V	
I <sub>OPH</sub>	Output High Peak Current	-1.0	A	4
I <sub>OPL</sub>	Output Low Peak Current	1.0	A	4
V <sub>CC</sub>	Supply voltage	35	V	

## Notes

1. AC for 1 minute, RH = 40 ~ 60%.
2. For 10 second peak
3. Exponential Waveform, I<sub>O(PEAK)</sub> ≤ |1.0A|, Pulse Width ≤ 0.3us
4. Pulse Width = 10us, Duty = 1.0%



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## Recommended Operating Conditions

Characteristics	Symbol	Min.	Typ.	Max.	Unit
Input Current	$I_{F(ON)}$	7.5	-	10	mA
Input Voltage	$V_{F(OFF)}$	0	-	0.8	V
Supply Voltage	$V_{CC}$	10	-	30	V
Peak Output Current	$I_{OPH}/I_{OPL}$	-	-	$\pm 1.0$	A
Operating Temperature	$T_{opr}$	-40	-	100	$^{\circ}C$

## Electrical Characteristics

Typical values are measured at  $V_{CC}=30V$ ,  $V_{EE}=Gnd$ ,  $T_A = -40^{\circ}C$  to  $100^{\circ}C$  (unless otherwise specified)

## Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$V_F$	Forward Voltage	$I_F = 5mA$	-	1.4	1.7	V	
$V_R$	Reverse Voltage	$I_R = 10\mu A$	5.0	-	-	V	
$\Delta V_F/\Delta T_A$	Temperature coefficient of forward voltage	$I_F = 5mA$	-	-1.7	-	mV/ $^{\circ}C$	

## Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$I_{CCL}$	Logic Low Supply Current	$V_F = 0$ to $0.8V$ , $V_O = Open$	-	1.95	3	mA	
$I_{CCH}$	Logic High Supply Current	$I_F = 7mA$ to $10mA$ , $V_O = Open$	-	1.98	3		

## Transfer Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$V_{OH}$	High Level Output Voltage	$I_F = 5mA$ , $I_O = -100mA$	$V_{CC}-4V$	$V_{CC}-0.3V$	-	V	
$V_{OL}$	Low Level Output Voltage	$V_{CC} = 30V$ , $I_O = 100mA$	-	0.28	1.0		
$I_{OPH}$	High Level Output Current	$V_{CC} = 30V$ , $V_{6-5} = 4V$ , $I_F = 5mA$	-	-1	-0.5	A	
		$V_{CC} = 30V$ , $V_{6-5} = 15V$ , $I_F = 5mA$	-	-1.8	-1.0		
$I_{OPL}$	Low Level Output Current	$V_{CC} = 30V$ , $V_{6-5} = 2.5V$ , $I_F = 0mA$	0.5	0.75	-	A	
		$V_{CC} = 30V$ , $V_{6-5} = 10V$ , $I_F = 0mA$	1.0	1.5	-		
$I_{FLH}$	Input Threshold Current	$V_O > 5V$ , $V_{CC} = 30V$	-	2.6	5	mA	
$V_{FHL}$	Input Threshold Voltage	$V_O < 5V$ , $V_{CC} = 30V$	0.8	-	-	V	



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## Electrical Characteristics

Typical values are measured at  $V_{CC}=30V$ ,  $V_{EE}=Gnd$ ,  $T_A = -40^{\circ}C$  to  $100^{\circ}C$  (unless otherwise specified)

## Switching Characteristics

Symbol	Parameters	Test Conditions		Min	Typ	Max	Units	Notes
$T_{PHL}$	High to Low Propagation Delay	$I_F = 7$ to $16mA$ , $C_g = 3nF$ , $R_g = 47\Omega$		-	110	200	ns	
$T_{PLH}$	Low to High Propagation Delay			-	120	200	ns	
$P_{WD}$	Pulse Width Distortion			-	-	45	ns	
$t_{PSK}$	Propagation Delay Skew			-	-	38	ns	
$t_r$	Rise Time			-	30	100	ns	
$t_f$	Fall Time			-	15	60	ns	
$ CM_H $	Common Mode Transient High	$V_{CC} = 30V$ , $T_A = 25^{\circ}C$ ,	$I_F = 7$ to $16mA$ $V_{O(min)} = 26V$	-20	-	-	$kV/\mu s$	
$ CM_L $	Common Mode Transient Low	$V_{CM} = 1kV$	$I_F = 0mA$ $V_{O(max)} = 1V$	20	-	-	$kV/\mu s$	



Typical Characteristic Curves

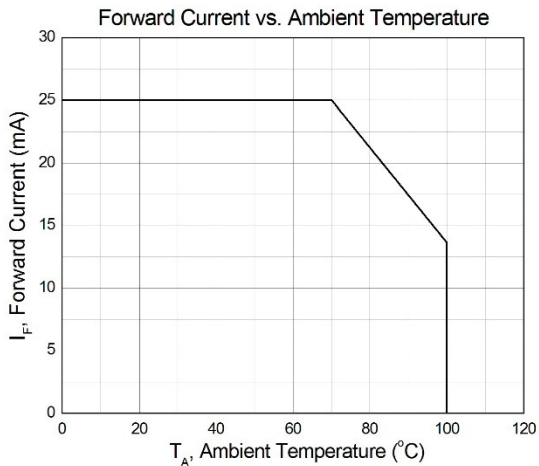


Figure 1

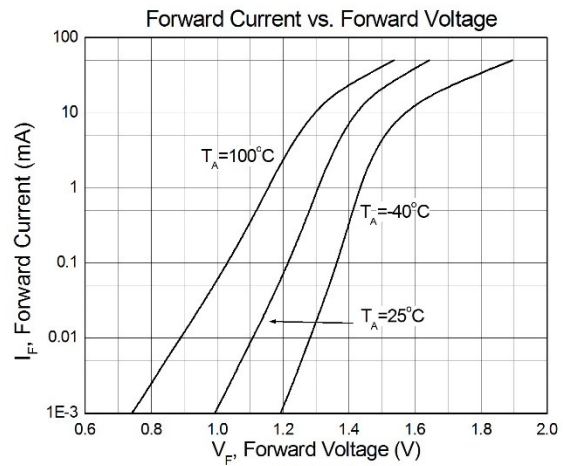


Figure 2

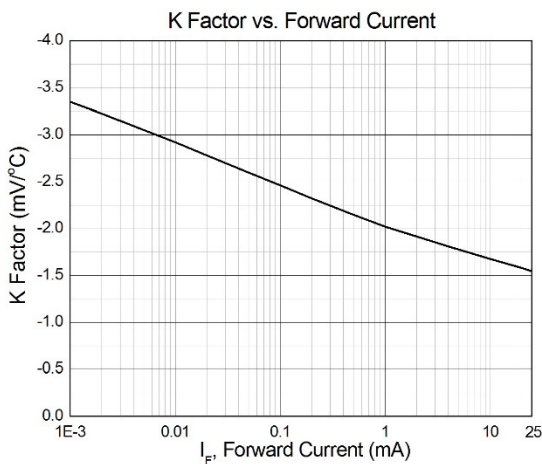


Figure 3

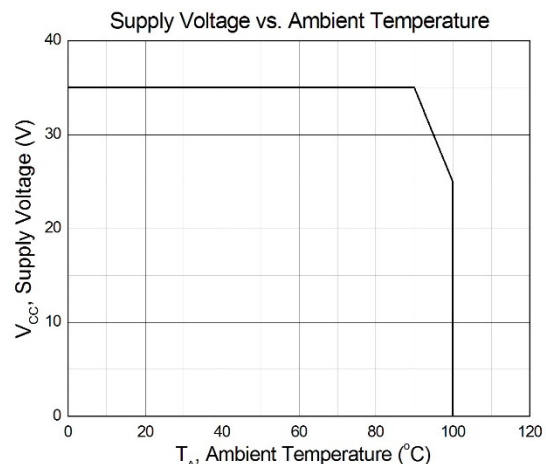


Figure 4

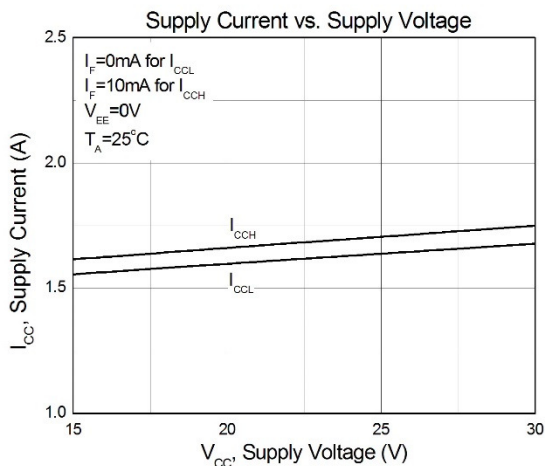


Figure 5

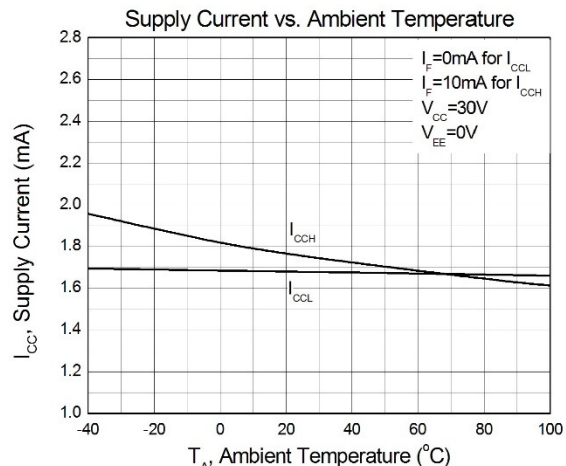


Figure 6



# 1.0A MOSFET/IGBT Gate Driver Optocoupler

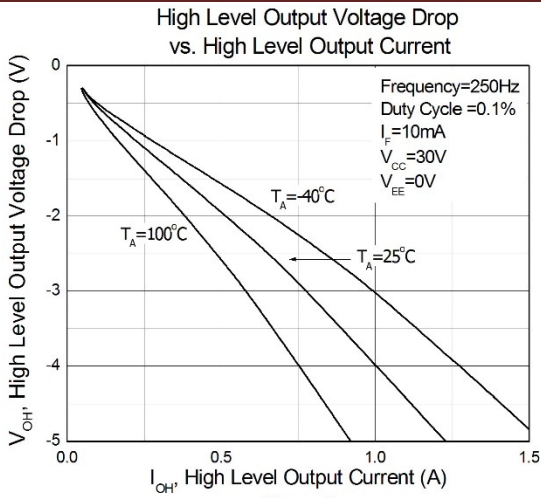


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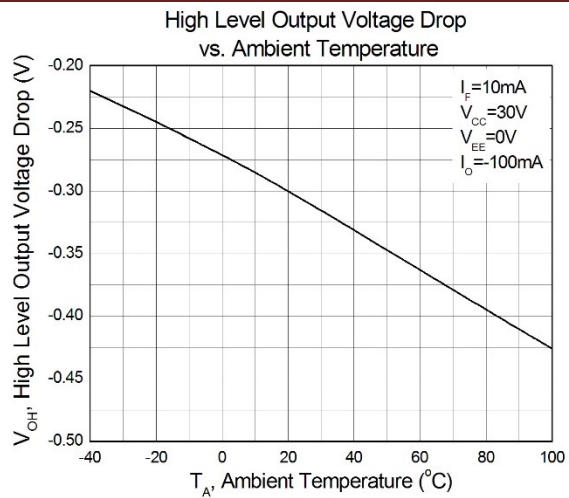


Figure 8

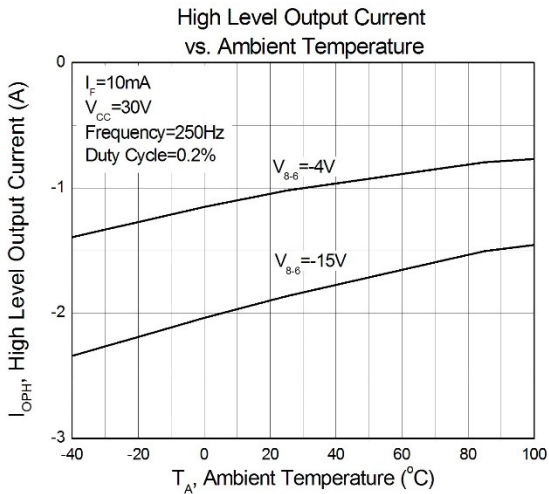


Figure 9

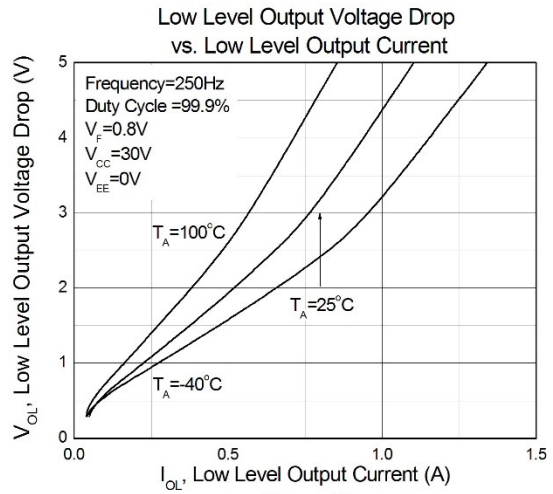


Figure 10

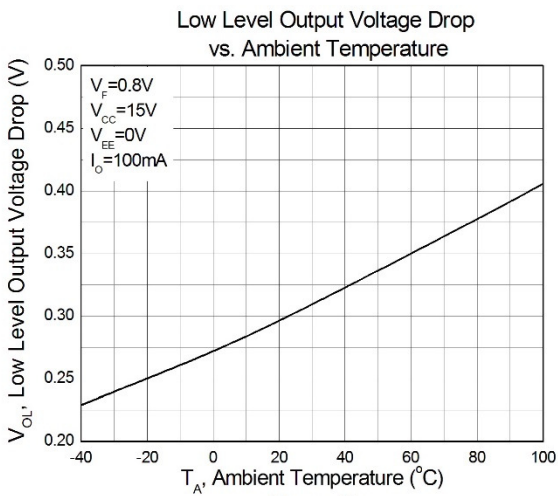


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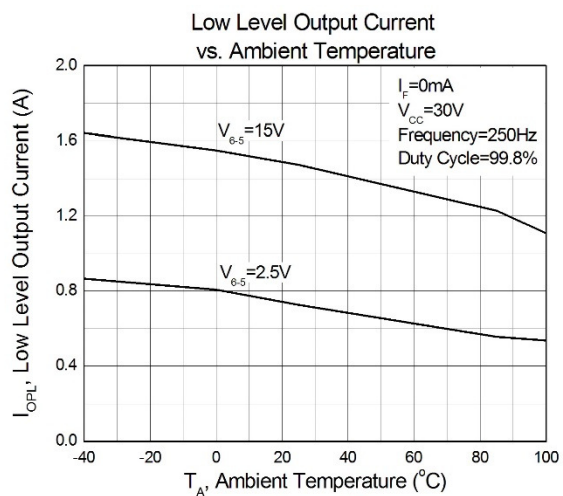


Figure 12



# 1.0A MOSFET/IGBT Gate Driver Optocoupler

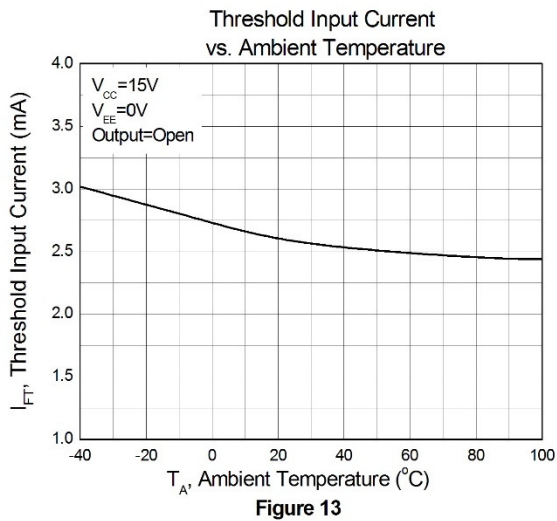


Figure 13

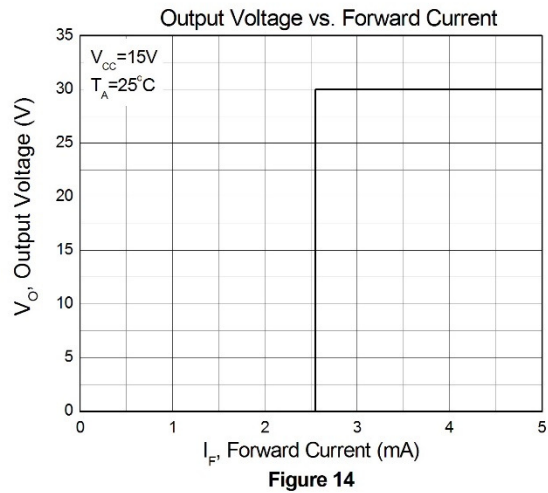


Figure 14

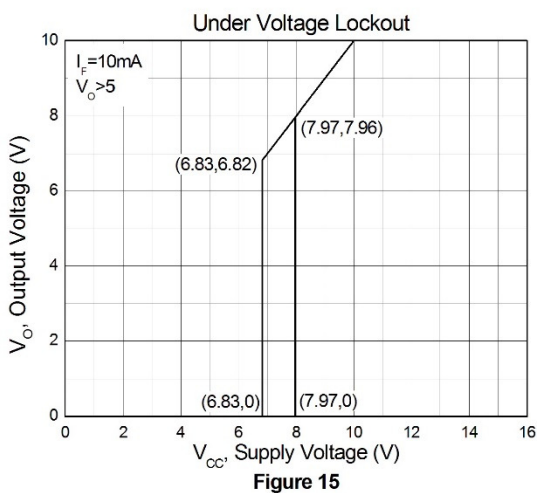


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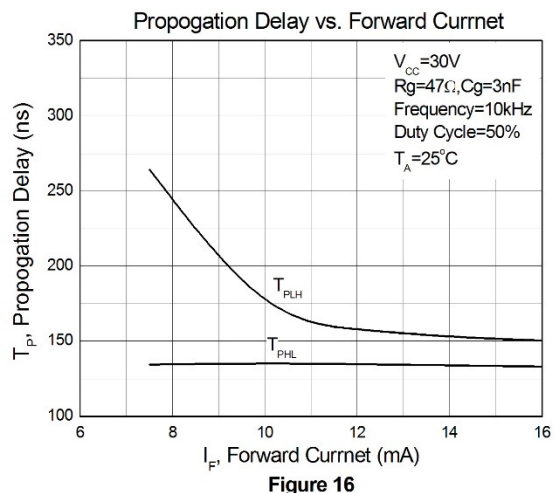


Figure 16

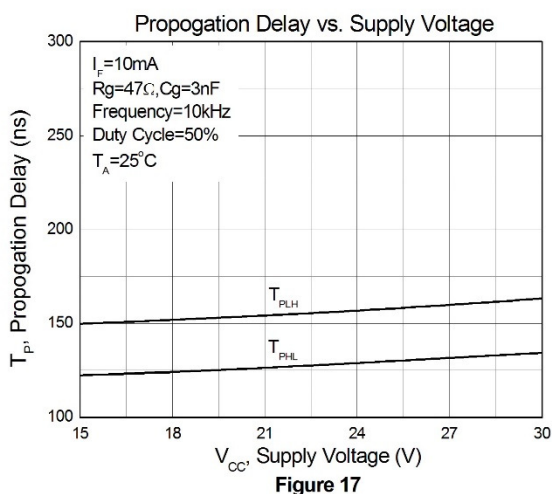


Figure 17

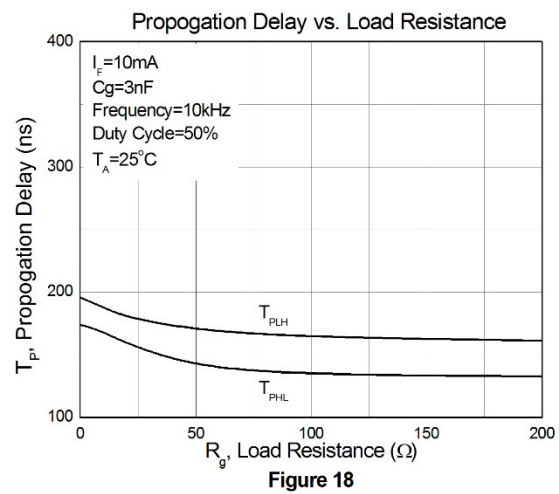


Figure 18



# 1.0A MOSFET/IGBT Gate Driver Optocoupler

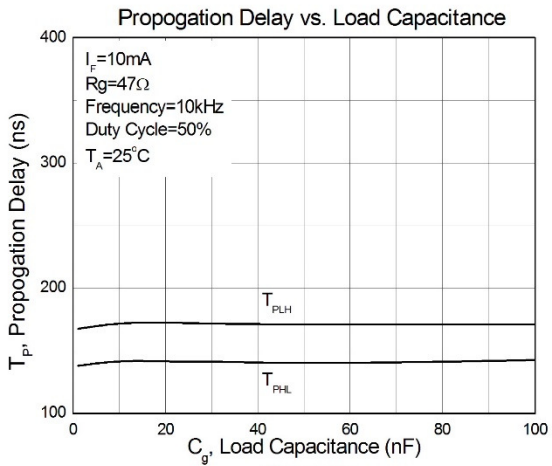


Figure 19

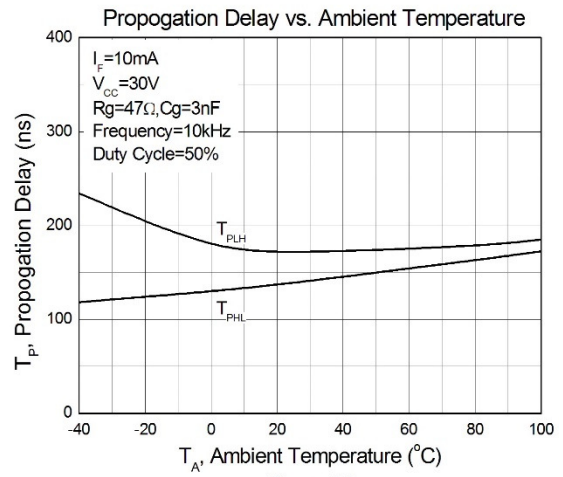


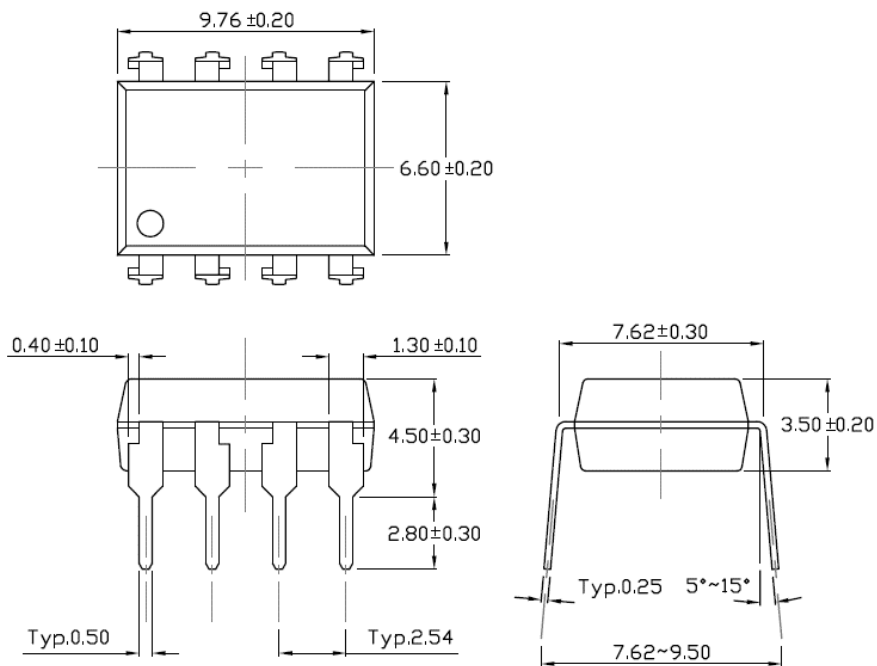
Figure 20



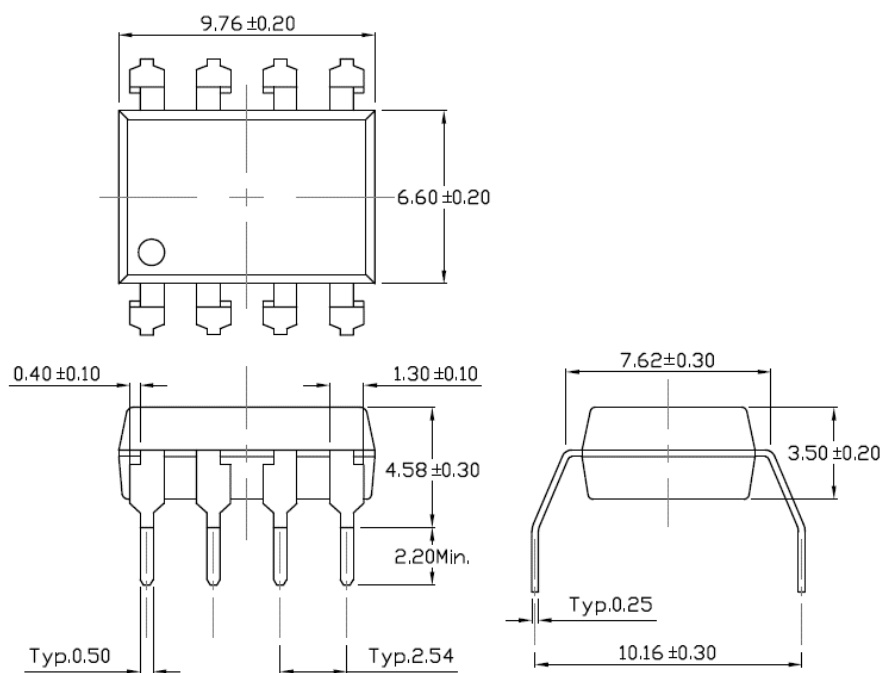


**Package Dimension** *Dimensions in mm unless otherwise stated*

**Standard DIP – Through Hole**



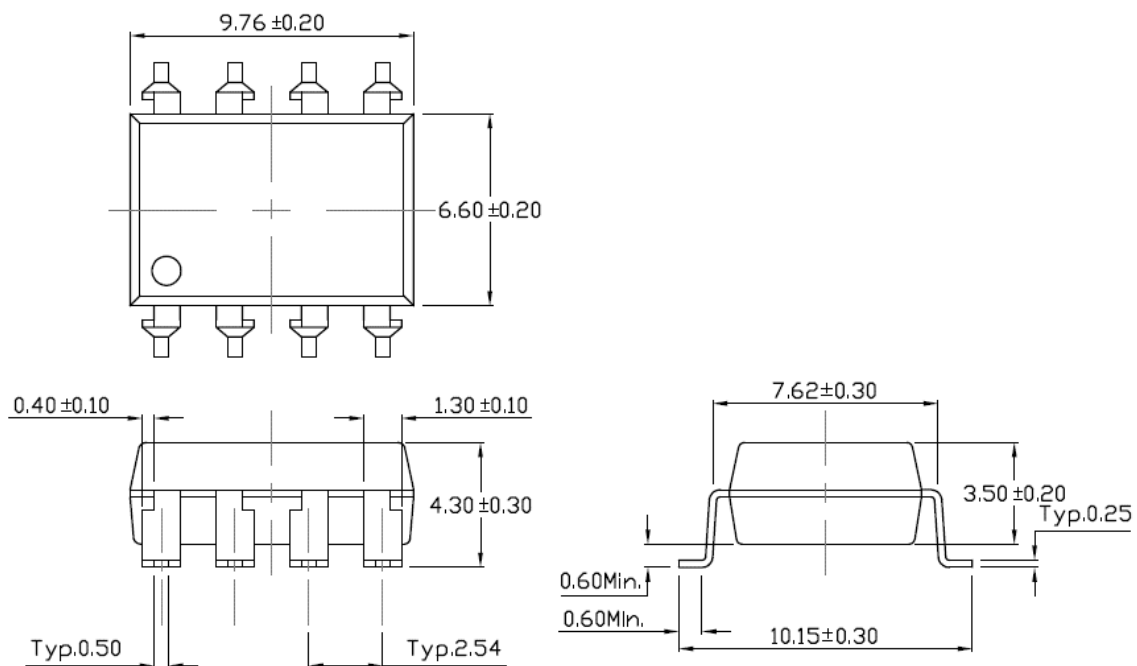
**Gullwing (400mil) Lead Forming – Through Hole (M Type)**



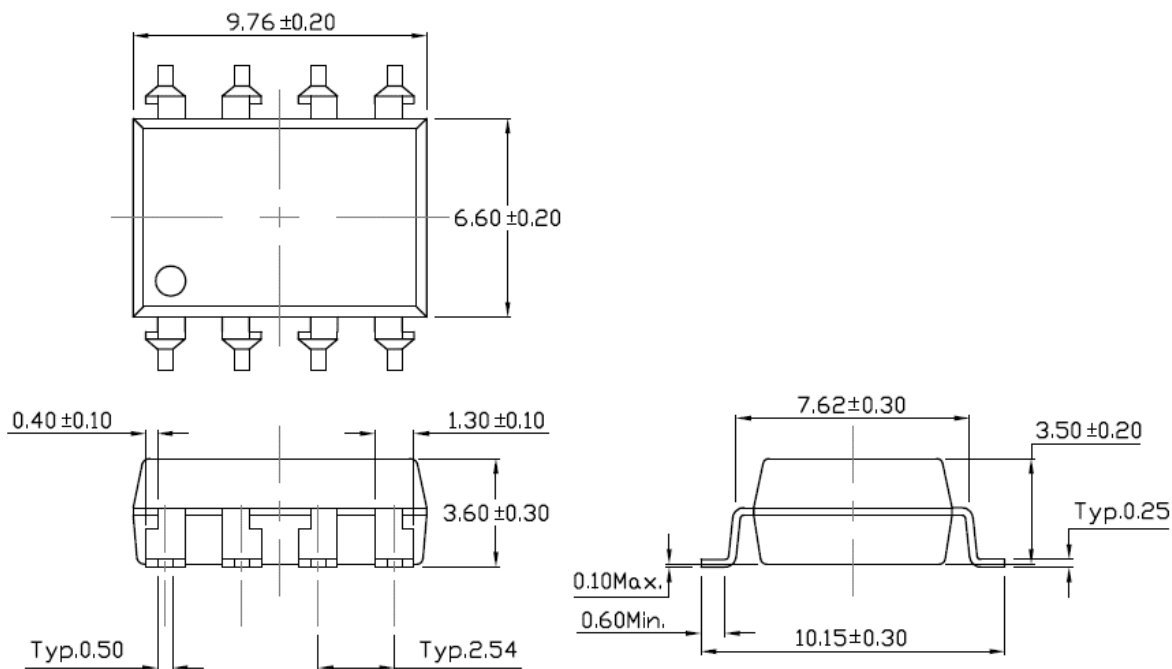


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## Surface Mount Lead Forming (S Type)



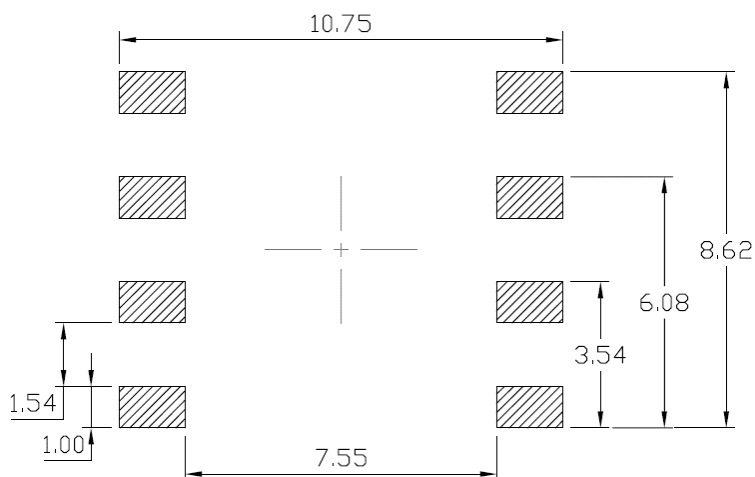
## Surface Mount (Low Profile) Lead Forming (SL Type)



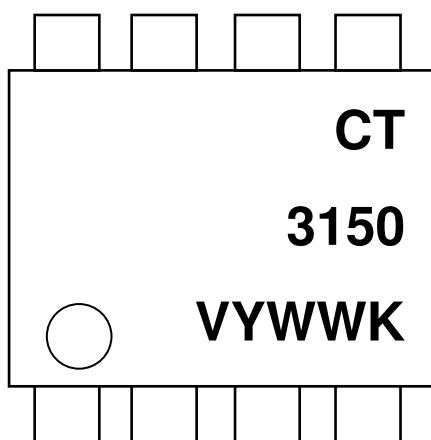


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## Recommended Solder Mask Dimensions in mm unless otherwise stated



## Device Marking



- CT : Denotes "CT Micro"
- 3150 : Product Number
- V : VDE Option
- Y : Fiscal Year
- WW : Work Week
- K : Production Code

**1.0A MOSFET/IGBT Gate Driver Optocoupler****Ordering Information**

CT3150(V)(Y)(Z)

V = VDE Option ( V or None)

Y = Lead form option (S, SL, M or none)

Z = Tape and reel option (T1, T2 or none)

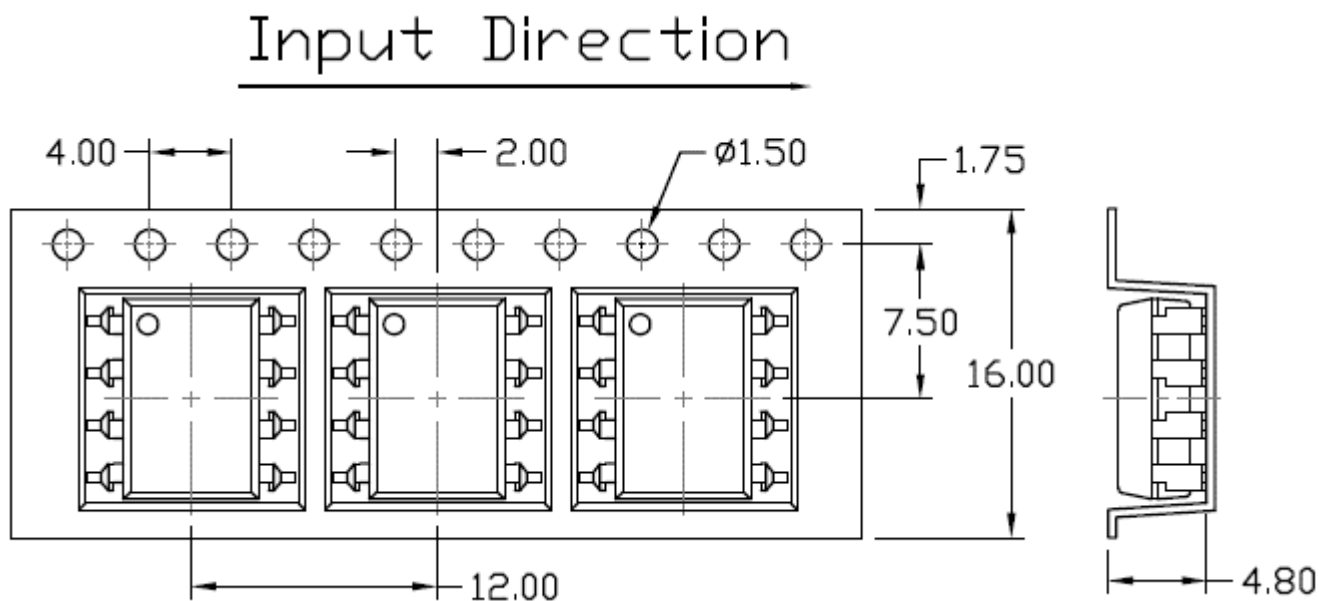
<b>Option</b>	<b>Description</b>	<b>Quantity</b>
None	Standard 8 Pin Dip	40 Units/Tube
M	Gullwing (400mil) Lead Forming	40 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1000 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1000 Units/Reel



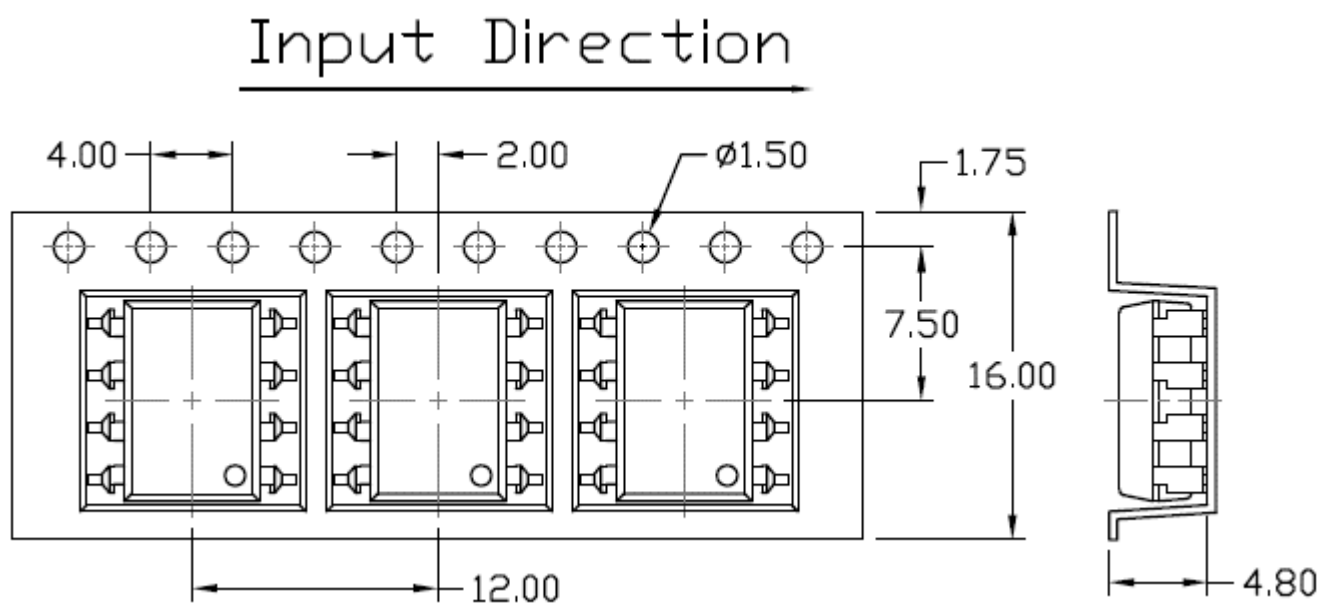
# 1.0A MOSFET/IGBT Gate Driver Optocoupler

## Carrier Tape Specifications *Dimensions in mm unless otherwise stated*

### Option S(T1) & SL(T1)



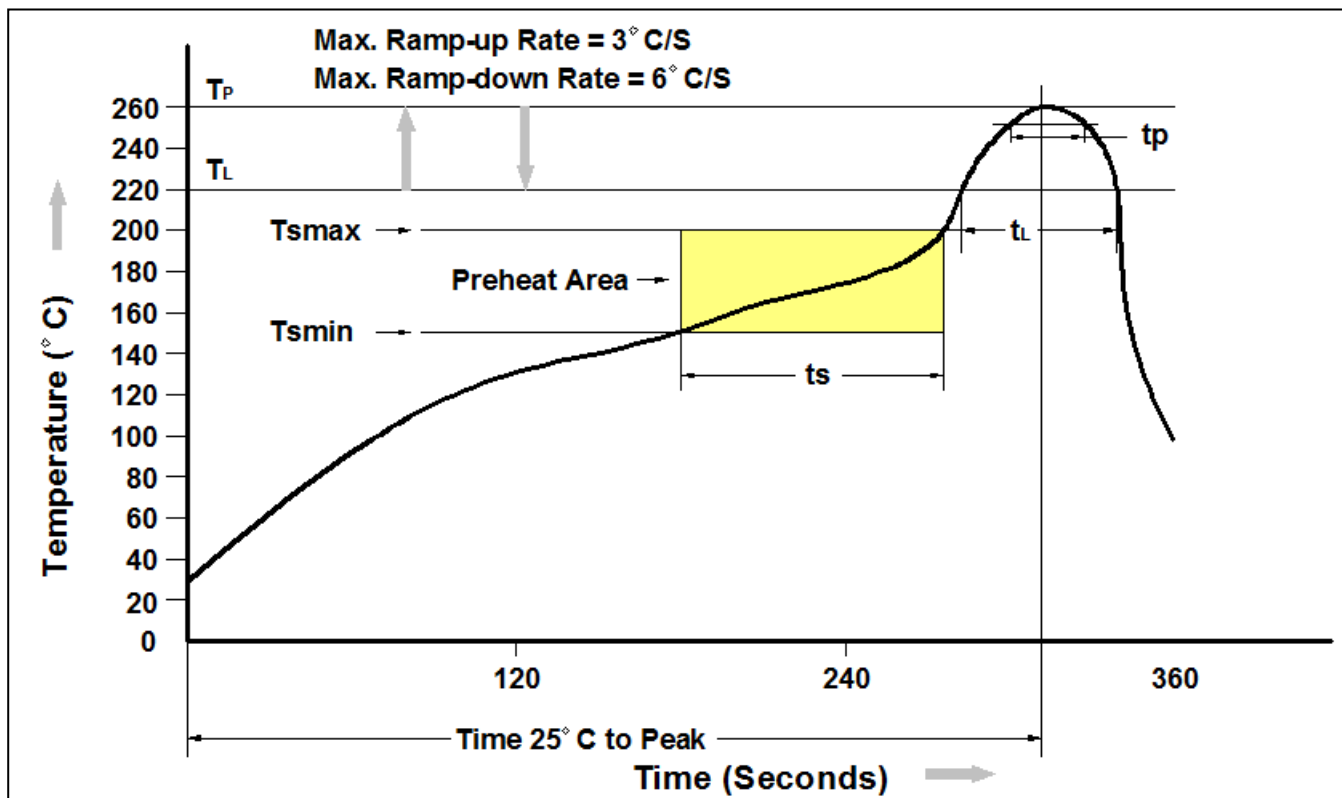
### Option S(T2) & SL(T2)





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## Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmín)	150°C
Temperature Max. (Tsmáx)	200°C
Time (ts) from (Tsmín to Tsmáx)	60-120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.*